

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

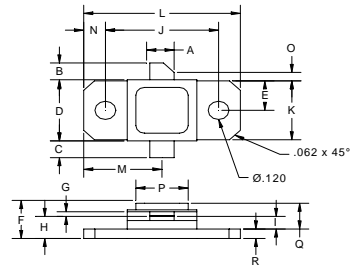
The **ASI MZ0912B100Y** is Designed for General Purpose Class C Power Amplifier Applications up to 1215 MHz.

FEATURES:

- $P_G = 7.0$ dB min.at 100 W / 1215 MHz
- Common Base
- **Omnigold™** Metalization System

MAXIMUM RATINGS

V_{CE}	20 V
V_{CB}	65 V
V_{EB}	3.0 V
I_C	6.0 A
P_{DISS}	290 W @ $T_{mb} = 75^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.43 K/W

PACKAGE STYLE .400 2L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.140 / 3.56	
B	.110 / 2.80	
C	.110 / 2.80	
D	.395 / 10.03	.407 / 10.34
E	.193 / 4.90	
F		.230 / 5.84
G	.003 / 0.08	.006 / 0.15
H	.118 / 3.00	.131 / 3.33
I		.063 / 1.60
J		.650 / 16.51
K		.386 / 9.80
L		.900 / 22.86
M		.450 / 11.43
N		.125 / 3.18
O	.050 / 1.27	
P		.405 / 10.29
Q		.170 / 4.32
R		.062 / 1.58

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 65$ V			40	mA
I_{CBO}	$V_{CB} = 50$ V			4	mA
I_{CES}	$V_{CE} = 60$ V			40	mA
I_{EBO}	$V_{EB} = 1.5$ V			400	μA
P_G	$V_{CC} = 50$ $P_{OUT} = 100$ W $f = 960 - 1215$ MHz	7.0			dB
η_c		42			%